



Welcome to [E-XFL.COM](https://www.e-xfl.com)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Not For New Designs
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, I ² C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	79
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	24K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 28x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc560b40l3b3edx

3.16	RESET electrical characteristics	57
3.17	Power management electrical characteristics	60
3.17.1	Voltage regulator electrical characteristics	60
3.17.2	Low voltage detector electrical characteristics	65
3.18	Power consumption	66
3.19	Flash memory electrical characteristics	68
3.19.1	Program/Erase characteristics	68
3.19.2	Flash power supply DC characteristics	69
3.19.3	Start-up/Switch-off timings	70
3.20	Electromagnetic compatibility (EMC) characteristics	70
3.20.1	Designing hardened software to avoid noise problems	70
3.20.2	Electromagnetic interference (EMI)	71
3.20.3	Absolute maximum ratings (electrical sensitivity)	71
3.21	Fast external crystal oscillator (4 to 16 MHz) electrical characteristics	72
3.22	Slow external crystal oscillator (32 kHz) electrical characteristics	75
3.23	FMPLL electrical characteristics	77
3.24	Fast internal RC oscillator (16 MHz) electrical characteristics	78
3.25	Slow internal RC oscillator (128 kHz) electrical characteristics	79
3.26	ADC electrical characteristics	80
3.26.1	Introduction	80
3.26.2	Input impedance and ADC accuracy	80
3.26.3	ADC electrical characteristics	85
3.27	On-chip peripherals	87
3.27.1	Current consumption	87
3.27.2	DSPI characteristics	88
3.27.3	Nexus characteristics	96
3.27.4	JTAG characteristics	98
4	Package characteristics	99
4.1	ECOPACK®	99
4.2	Package mechanical data	99
4.2.1	LQFP64	99
4.2.2	LQFP100	101
4.2.3	LQFP144	102
4.2.4	LBGA208	104

List of tables

Table 1.	Device summary	1
Table 2.	SPC560B40x/50x and SPC560C40x/50x device comparison	9
Table 3.	SPC560B40x/50x and SPC560C40x/50x series block summary	13
Table 4.	Voltage supply pin descriptions	19
Table 5.	System pin descriptions	20
Table 6.	Functional port pin descriptions	21
Table 7.	Nexus 2+ pin descriptions	39
Table 8.	Parameter classifications	40
Table 9.	PAD3V5V field description	40
Table 10.	OSCILLATOR_MARGIN field description	41
Table 11.	WATCHDOG_EN field description	41
Table 12.	Absolute maximum ratings	41
Table 13.	Recommended operating conditions (3.3 V)	42
Table 14.	Recommended operating conditions (5.0 V)	43
Table 15.	LQFP thermal characteristics	44
Table 16.	I/O input DC electrical characteristics	47
Table 17.	I/O pull-up/pull-down DC electrical characteristics	48
Table 18.	SLOW configuration output buffer electrical characteristics	48
Table 19.	MEDIUM configuration output buffer electrical characteristics	49
Table 20.	FAST configuration output buffer electrical characteristics	50
Table 21.	Output pin transition times	50
Table 22.	I/O supply segment	51
Table 23.	I/O consumption	52
Table 24.	I/O weight	53
Table 25.	Reset electrical characteristics	58
Table 26.	Voltage regulator electrical characteristics	63
Table 27.	Low voltage detector electrical characteristics	66
Table 28.	Power consumption on VDD_BV and VDD_HV	66
Table 29.	Program and erase specifications	68
Table 30.	Flash module life	68
Table 31.	Flash read access timing	69
Table 32.	Flash memory power supply DC electrical characteristics	69
Table 33.	Start-up time/Switch-off time	70
Table 34.	EMI radiated emission measurement	71
Table 35.	ESD absolute maximum ratings	71
Table 36.	Latch-up results	72
Table 37.	Crystal description	73
Table 38.	Fast external crystal oscillator (4 to 16 MHz) electrical characteristics	74
Table 39.	Crystal motional characteristics	76
Table 40.	Slow external crystal oscillator (32 kHz) electrical characteristics	77
Table 41.	FMPLL electrical characteristics	77
Table 42.	Fast internal RC oscillator (16 MHz) electrical characteristics	78
Table 43.	Slow internal RC oscillator (128 kHz) electrical characteristics	79
Table 44.	ADC input leakage current	85
Table 45.	ADC conversion characteristics	86
Table 46.	On-chip peripherals current consumption	88
Table 47.	DSPI characteristics	90
Table 48.	Nexus characteristics	96

Table 2. SPC560B40x/50x and SPC560C40x/50x device comparison⁽¹⁾

Feature	Device										
	SPC560B 40L1	SPC560B 40L3	SPC560B 40L5	SPC560C 40L1	SPC560C 40L3	SPC560B 50L1	SPC560B 50L3	SPC560B 50L5	SPC560C 50L1	SPC560C 50L3	SPC560B 50B2
CPU	e200z0h										
Execution speed ⁽²⁾	Static – up to 64 MHz										
Code Flash	256 KB					512 KB					
Data Flash	64 KB (4 × 16 KB)										
RAM	24 KB			32 KB		32 KB			48 KB		
MPU	8-entry										
ADC (10-bit)	12 ch	28 ch	36 ch	8 ch	28 ch	12 ch	28 ch	36 ch	8 ch	28 ch	36 ch
CTU	Yes										
Total timer I/O ⁽³⁾ eMIOS	12 ch, 16-bit	28 ch, 16-bit	56 ch, 16-bit	12 ch, 16-bit	28 ch, 16-bit	12 ch, 16-bit	28 ch, 16-bit	56 ch, 16-bit	12 ch, 16-bit	28 ch, 16-bit	56 ch, 16-bit
– PWM + MC + IC/OC ⁽⁴⁾	2 ch	5 ch	10 ch	2 ch	5 ch	2 ch	5 ch	10 ch	2 ch	5 ch	10 ch
– PWM + IC/OC ⁽⁴⁾	10 ch	20 ch	40 ch	10 ch	20 ch	10 ch	20 ch	40 ch	10 ch	20 ch	40 ch
– IC/OC ⁽⁴⁾	—	3 ch	6 ch	—	3 ch	—	3 ch	6 ch	—	3 ch	6 ch
SCI (LINFlex)	3 ⁽⁵⁾			4							
SPI (DSPI)	2	3		2	3	2	3		2	3	
CAN (FlexCAN)	2 ⁽⁶⁾			5	6	3 ⁽⁷⁾			5	6	
I ² C	1										
32 kHz oscillator	Yes										
GPIO ⁽⁸⁾	45	79	123	45	79	45	79	123	45	79	123

Table 3. SPC560B40x/50x and SPC560C40x/50x series block summary

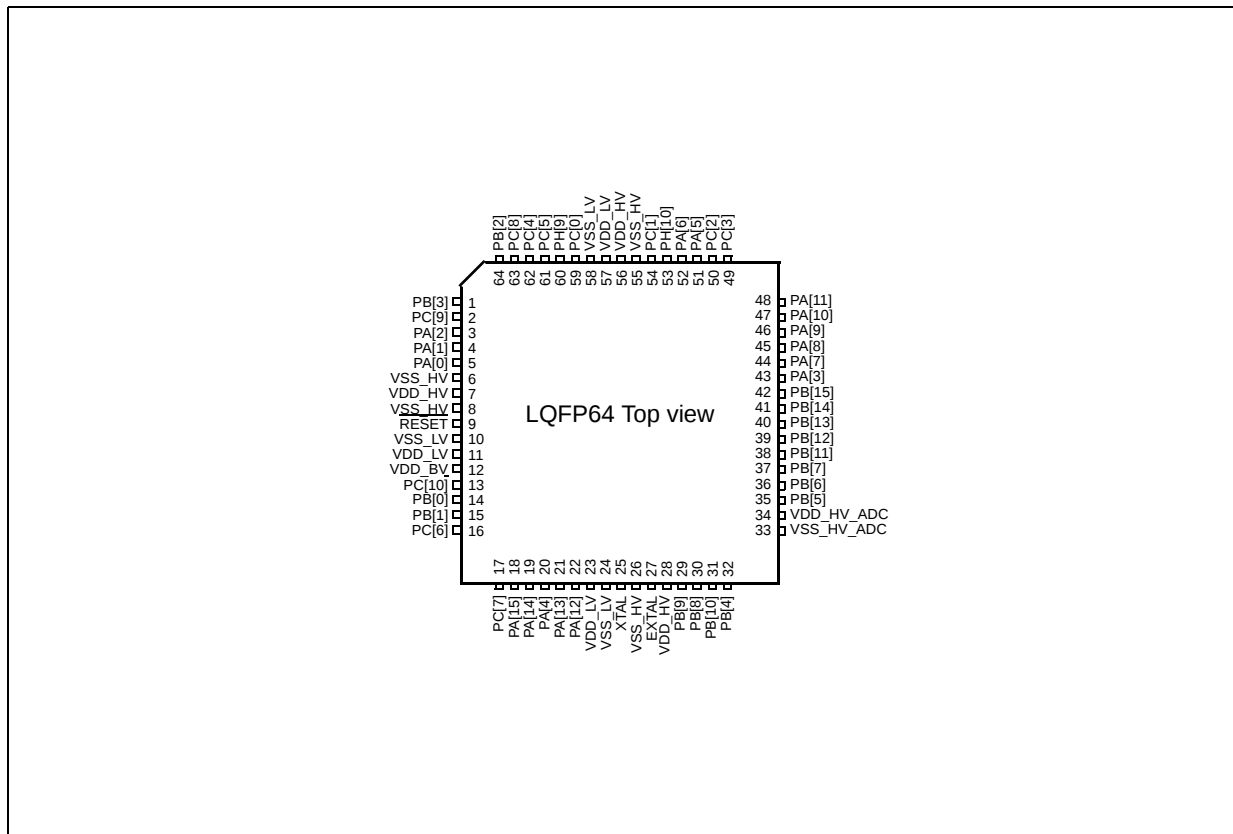
Block	Function
Analog-to-digital converter (ADC)	Multi-channel, 10-bit analog-to-digital converter
Boot assist module (BAM)	A block of read-only memory containing VLE code which is executed according to the boot mode of the device
Clock monitor unit (CMU)	Monitors clock source (internal and external) integrity
Cross triggering unit (CTU)	Enables synchronization of ADC conversions with a timer event from the eMIOS or from the PIT
Deserial serial peripheral interface (DSPI)	Provides a synchronous serial interface for communication with external devices
Error Correction Status Module (ECSM)	Provides a myriad of miscellaneous control functions for the device including program-visible information about configuration and revision levels, a reset status register, wakeup control for exiting sleep modes, and optional features such as information on memory errors reported by error-correcting codes
Enhanced Direct Memory Access (eDMA)	Performs complex data transfers with minimal intervention from a host processor via “n” programmable channels.
Enhanced modular input output system (eMIOS)	Provides the functionality to generate or measure events
Flash memory	Provides non-volatile storage for program code, constants and variables
FlexCAN (controller area network)	Supports the standard CAN communications protocol
Frequency-modulated phase-locked loop (FMPLL)	Generates high-speed system clocks and supports programmable frequency modulation
Internal multiplexer (IMUX) SIU subblock	Allows flexible mapping of peripheral interface on the different pins of the device
Inter-integrated circuit (I ² C™) bus	A two wire bidirectional serial bus that provides a simple and efficient method of data exchange between devices
Interrupt controller (INTC)	Provides priority-based preemptive scheduling of interrupt requests
JTAG controller	Provides the means to test chip functionality and connectivity while remaining transparent to system logic when not in test mode
LINFlex controller	Manages a high number of LIN (Local Interconnect Network protocol) messages efficiently with a minimum of CPU load
Clock generation module (MC_CGM)	Provides logic and control required for the generation of system and peripheral clocks
Mode entry module (MC_ME)	Provides a mechanism for controlling the device operational mode and mode transition sequences in all functional states; also manages the power control unit, reset generation module and clock generation module, and holds the configuration, control and status registers accessible for applications
Power control unit (MC_PCU)	Reduces the overall power consumption by disconnecting parts of the device from the power supply via a power switching device; device components are grouped into sections called “power domains” which are controlled by the PCU
Reset generation module (MC_RGM)	Centralizes reset sources and manages the device reset sequence of the device

3 Package pinouts and signal descriptions

3.1 Package pinouts

The available LQFP pinouts and the LPGA208 ballmap are provided in the following figures. For pin signal descriptions, please refer to the device reference manual (RM0017).

Figure 2. LQFP 64-pin configuration^(a)



a. All LQFP64 information is indicative and must be confirmed during silicon validation.

Figure 4. LQFP 144-pin configuration

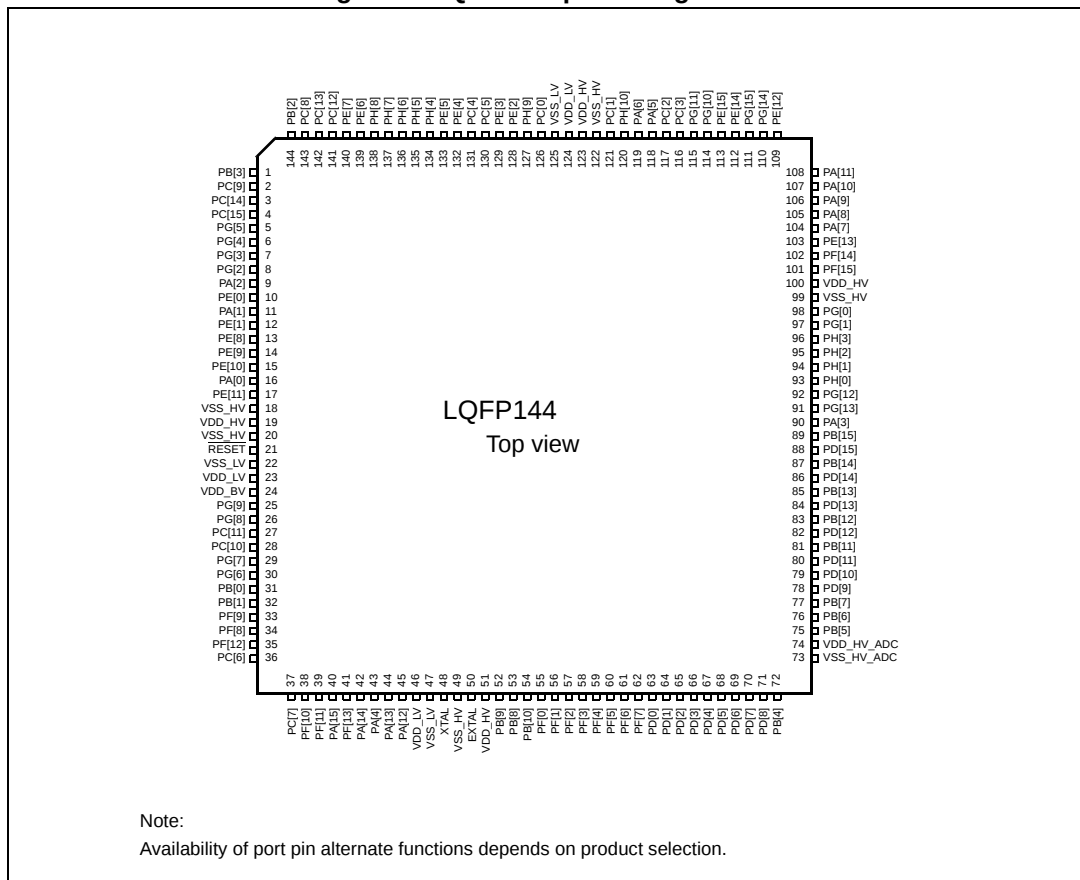


Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ⁽¹⁾	Function	Peripheral	I/O direction ⁽²⁾	Pad type	RESET configuration	Pin number			
								LQFP64	LQFP100	LQFP144	LBGA208 ⁽³⁾
PF[2]	PCR[82]	AF0 AF1 AF2 AF3 —	GPIO[82] E0UC[12] CS0_2 — ANS[10]	SIUL eMIOS_0 DSPI_2 — ADC	I/O I/O I/O — I	J	Tristate	—	—	57	T10
PF[3]	PCR[83]	AF0 AF1 AF2 AF3 —	GPIO[83] E0UC[13] CS1_2 — ANS[11]	SIUL eMIOS_0 DSPI_2 — ADC	I/O I/O O — I	J	Tristate	—	—	58	R10
PF[4]	PCR[84]	AF0 AF1 AF2 AF3 —	GPIO[84] E0UC[14] CS2_2 — ANS[12]	SIUL eMIOS_0 DSPI_2 — ADC	I/O I/O O — I	J	Tristate	—	—	59	N11
PF[5]	PCR[85]	AF0 AF1 AF2 AF3 —	GPIO[85] E0UC[22] CS3_2 — ANS[13]	SIUL eMIOS_0 DSPI_2 — ADC	I/O I/O O — I	J	Tristate	—	—	60	P11
PF[6]	PCR[86]	AF0 AF1 AF2 AF3 —	GPIO[86] E0UC[23] — — ANS[14]	SIUL eMIOS_0 — — ADC	I/O I/O — — I	J	Tristate	—	—	61	T11
PF[7]	PCR[87]	AF0 AF1 AF2 AF3 —	GPIO[87] — — — ANS[15]	SIUL — — — ADC	I/O — — — I	J	Tristate	—	—	62	R11
PF[8]	PCR[88]	AF0 AF1 AF2 AF3	GPIO[88] CAN3TX ⁽¹⁴⁾ CS4_0 CAN2TX ⁽¹⁵⁾	SIUL FlexCAN_3 DSPI_0 FlexCAN_2	I/O O O O	M	Tristate	—	—	34	P1

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ⁽¹⁾	Function	Peripheral	I/O direction ⁽²⁾	Pad type	RESET configuration	Pin number			
								LQFP64	LQFP100	LQFP144	LBGA208 ⁽³⁾
PG[0]	PCR[96]	AF0 AF1 AF2 AF3	GPIO[96] CAN5TX ⁽¹¹⁾ E1UC[23] —	SIUL FlexCAN_5 eMIOS_1 —	I/O O I/O —	M	Tristate	—	—	98	E14
PG[1]	PCR[97]	AF0 AF1 AF2 AF3 — —	GPIO[97] — E1UC[24] — CAN5RX ⁽¹¹⁾ EIRQ[14]	SIUL — eMIOS_1 — FlexCAN_5 SIUL	I/O — I/O — I I	S	Tristate	—	—	97	E13
PG[2]	PCR[98]	AF0 AF1 AF2 AF3	GPIO[98] E1UC[11] — —	SIUL eMIOS_1 — —	I/O I/O — —	M	Tristate	—	—	8	E4
PG[3]	PCR[99]	AF0 AF1 AF2 AF3 —	GPIO[99] E1UC[12] — — WKPU[17] ⁽⁴⁾	SIUL eMIOS_1 — — WKPU	I/O I/O — — I	S	Tristate	—	—	7	E3
PG[4]	PCR[100]	AF0 AF1 AF2 AF3	GPIO[100] E1UC[13] — —	SIUL eMIOS_1 — —	I/O I/O — —	M	Tristate	—	—	6	E1
PG[5]	PCR[101]	AF0 AF1 AF2 AF3 —	GPIO[101] E1UC[14] — — WKPU[18] ⁽⁴⁾	SIUL eMIOS_1 — — WKPU	I/O I/O — — I	S	Tristate	—	—	5	E2
PG[6]	PCR[102]	AF0 AF1 AF2 AF3	GPIO[102] E1UC[15] — —	SIUL eMIOS_1 — —	I/O I/O — —	M	Tristate	—	—	30	M2

Table 15. LQFP thermal characteristics⁽¹⁾ (continued)

Symbol		C	Parameter	Conditions ⁽²⁾	Pin count	Value	Unit
$R_{\theta JC}$	CC	D	Thermal resistance, junction-to-case ⁽⁵⁾	Single-layer board - 1s	64	11	°C/W
					100	22	
					144	22	
				Four-layer board - 2s2p	64	11	
					100	22	
					144	22	
Ψ_{JB}	CC	D	Junction-to-board thermal characterization parameter, natural convection	Single-layer board - 1s	64	TBD	°C/W
					100	33	
					144	34	
				Four-layer board - 2s2p	64	TBD	
					100	34	
					144	35	
Ψ_{JC}	CC	D	Junction-to-case thermal characterization parameter, natural convection	Single-layer board - 1s	64	TBD	°C/W
					100	9	
					144	10	
				Four-layer board - 2s2p	64	TBD	
					100	9	
					144	10	

1. Thermal characteristics are based on simulation.
2. $V_{DD} = 3.3\text{ V} \pm 10\% / 5.0\text{ V} \pm 10\%$, $T_A = -40$ to $125\text{ }^{\circ}\text{C}$
3. Junction-to-ambient thermal resistance determined per JEDEC JESD51-3 and JESD51-6. Thermal test board meets JEDEC specification for this package.
4. Junction-to-board thermal resistance determined per JEDEC JESD51-8. Thermal test board meets JEDEC specification for the specified package.
5. Junction-to-case at the top of the package determined using MIL-STD 883 Method 1012.1. The cold plate temperature is used for the case temperature. Reported value includes the thermal resistance of the interface layer.

3.14.2 Power considerations

The average chip-junction temperature, T_J , in degrees Celsius, may be calculated using [Equation 1](#):

$$\text{Equation 1 } T_J = T_A + (P_D \times R_{\theta JA})$$

Where:

T_A is the ambient temperature in $^{\circ}\text{C}$.

$R_{\theta JA}$ is the package junction-to-ambient thermal resistance, in $^{\circ}\text{C/W}$.

P_D is the sum of P_{INT} and $P_{I/O}$ ($P_D = P_{INT} + P_{I/O}$).

P_{INT} is the product of I_{DD} and V_{DD} , expressed in watts. This is the chip internal power.

$P_{I/O}$ represents the power dissipation on input and output pins; user determined.

Table 24. I/O weight⁽¹⁾ (continued)

Supply segment			Pad	LQFP144/LQFP100				LQFP64 ⁽²⁾			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
LQFP 144	LQFP 100	LQFP 64		SRC ⁽³⁾ = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
1	—	—	PG[9]	9%	—	10%	—	—	—	—	—
	—	—	PG[8]	9%	—	11%	—	—	—	—	—
	1	—	PC[11]	9%	—	11%	—	—	—	—	—
		1	PC[10]	9%	13%	11%	12%	9%	13%	11%	12%
	—	—	PG[7]	10%	14%	11%	12%	—	—	—	—
	—	—	PG[6]	10%	14%	12%	12%	—	—	—	—
	1	1	PB[0]	10%	14%	12%	12%	10%	14%	12%	12%
			PB[1]	10%	—	12%	—	10%	—	12%	—
	—	—	PF[9]	10%	—	12%	—	—	—	—	—
	—	—	PF[8]	10%	15%	12%	13%	—	—	—	—
	—	—	PF[12]	10%	15%	12%	13%	—	—	—	—
	1	1	PC[6]	10%	—	12%	—	10%	—	12%	—
			PC[7]	10%	—	12%	—	10%	—	12%	—
	—	—	PF[10]	10%	14%	12%	12%	—	—	—	—
	—	—	PF[11]	10%	—	11%	—	—	—	—	—
	1	1	PA[15]	9%	12%	10%	11%	9%	12%	10%	11%
	—	—	PF[13]	8%	—	10%	—	—	—	—	—
	1	1	PA[14]	8%	11%	9%	10%	8%	11%	9%	10%
			PA[4]	8%	—	9%	—	8%	—	9%	—
			PA[13]	7%	10%	9%	9%	7%	10%	9%	9%
			PA[12]	7%	—	8%	—	7%	—	8%	—

Table 28. Power consumption on VDD_BV and VDD_HV (continued)

Symbol		C	Parameter	Conditions ⁽¹⁾	Value			Unit	
					Min	Typ	Max		
I _{DDSTOP}	CC	P	STOP mode current ⁽⁷⁾	Slow internal RC oscillator (128 kHz) running	T _A = 25 °C	—	180	700 ⁽⁸⁾	μA
		D			T _A = 55 °C	—	500	—	
		D			T _A = 85 °C	—	1	6 ⁽⁸⁾	mA
		D			T _A = 105 °C	—	2	9 ⁽⁸⁾	
		P			T _A = 125 °C	—	4.5	12 ⁽⁸⁾	
I _{DDSTDBY2}	CC	P	STANDBY2 mode current ⁽⁹⁾	Slow internal RC oscillator (128 kHz) running	T _A = 25 °C	—	30	100	μA
		D			T _A = 55 °C	—	75	—	
		D			T _A = 85 °C	—	180	700	
		D			T _A = 105 °C	—	315	1000	
		P			T _A = 125 °C	—	560	1700	
I _{DDSTDBY1}	CC	T	STANDBY1 mode current ⁽¹⁰⁾	Slow internal RC oscillator (128 kHz) running	T _A = 25 °C	—	20	60	μA
		D			T _A = 55 °C	—	45	—	
		D			T _A = 85 °C	—	100	350	
		D			T _A = 105 °C	—	165	500	
		D			T _A = 125 °C	—	280	900	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified

2. I_{DDMAX} is drawn only from the V_{DD_BV} pin. Running consumption does not include I/Os toggling which is highly dependent on the application. The given value is thought to be a worst case value with all peripherals running, and code fetched from code flash while modify operation ongoing on data flash. Notice that this value can be significantly reduced by application: switch off not used peripherals (default), reduce peripheral frequency through internal prescaler, fetch from RAM most used functions, use low power mode when possible.

3. Higher current may be sinked by device during power-up and standby exit. Please refer to inrush current on [Table 26](#).

4. I_{DDRUN} is drawn only from the V_{DD_BV} pin. RUN current measured with typical application with accesses on both flash and RAM.

5. Only for the "P" classification: Data and Code Flash in Normal Power. Code fetched from RAM: Serial IPs CAN and LIN in loop back mode, DSPI as Master, PLL as system Clock (4 x Multiplier) peripherals on (eMIOS/CTU/ADC) and running at max frequency, periodic SW/WDG timer reset enabled.

6. Data Flash Power Down. Code Flash in Low Power. SIRC (128 kHz) and FIRC (16 MHz) on. 10 MHz XTAL clock. FlexCAN: instances: 0, 1, 2 ON (clocked but not reception or transmission), instances: 4, 5, 6 clock gated. LINFlex: instances: 0, 1, 2 ON (clocked but not reception or transmission), instance: 3 clock gated. eMIOS: instance: 0 ON (16 channels on PA[0]–PA[11] and PC[12]–PC[15]) with PWM 20 kHz, instance: 1 clock gated. DSPI: instance: 0 (clocked but no communication). RTC/API ON. PIT ON. STM ON. ADC ON but not conversion except 2 analog watchdog.

7. Only for the "P" classification: No clock, FIRC (16 MHz) off, SIRC (128 kHz) on, PLL off, HPVreg off, ULPVreg/LPVreg on. All possible peripherals off and clock gated. Flash in power down mode.

8. When going from RUN to STOP mode and the core consumption is > 6 mA, it is normal operation for the main regulator module to be kept on by the on-chip current monitoring circuit. This is most likely to occur with junction temperatures exceeding 125 °C and under these circumstances, it is possible for the current to initially exceed the maximum STOP specification by up to 2 mA. After entering stop, the application junction temperature will reduce to the ambient level and the main regulator will be automatically switched off when the load current is below 6 mA.

9. Only for the "P" classification: ULPreg on, HP/LPVreg off, 32 KB RAM on, device configured for minimum consumption, all possible modules switched off.

10. ULPreg on, HP/LPVreg off, 8 KB RAM on, device configured for minimum consumption, all possible modules switched off.

3.19 Flash memory electrical characteristics

3.19.1 Program/Erase characteristics

Table 29 shows the program and erase characteristics.

Table 29. Program and erase specifications

Symbol		C	Parameter	Value				Unit
				Min	Typ ⁽¹⁾	Initial max ⁽²⁾	Max ⁽³⁾	
T _{dwprogram}	CC	C	Double word (64 bits) program time ⁽⁴⁾	—	22	50	500	μs
T _{16Kpperase}			16 KB block preprogram and erase time	—	300	500	5000	ms
T _{32Kpperase}			32 KB block preprogram and erase time	—	400	600	5000	ms
T _{128Kpperase}			128 KB block preprogram and erase time	—	800	1300	7500	ms
T _{esus}	CC	D	Erase suspend latency	—	—	30	30	μs

1. Typical program and erase times assume nominal supply values and operation at 25 °C.
2. Initial factory condition: < 100 program/erase cycles, 25 °C, typical supply voltage.
3. The maximum program and erase times occur after the specified number of program/erase cycles. These maximum values are characterized but not guaranteed.
4. Actual hardware programming times. This does not include software overhead.

Table 30. Flash module life

Symbol		C	Parameter	Conditions	Value			Unit
					Min	Typ	Max	
P/E	CC	C	Number of program/erase cycles per block over the operating temperature range (T _j)	16 KB blocks	100000	—	—	cycles
				32 KB blocks	10000	100000	—	
				128 KB blocks	1000	100000	—	
Retention	CC	C	Minimum data retention at 85 °C average ambient temperature ⁽¹⁾	Blocks with 0–1000 P/E cycles	20	—	—	years
				Blocks with 1001–10000 P/E cycles	10	—	—	
				Blocks with 10001–100000 P/E cycles	5	—	—	

1. Ambient temperature averaged over duration of application, not to exceed recommended product operating temperature range.

ECC circuitry provides correction of single bit faults and is used to improve further automotive reliability results. Some units will experience single bit corrections throughout the life of the product with no impact to product reliability.

Figure 13. Crystal oscillator and resonator connection scheme

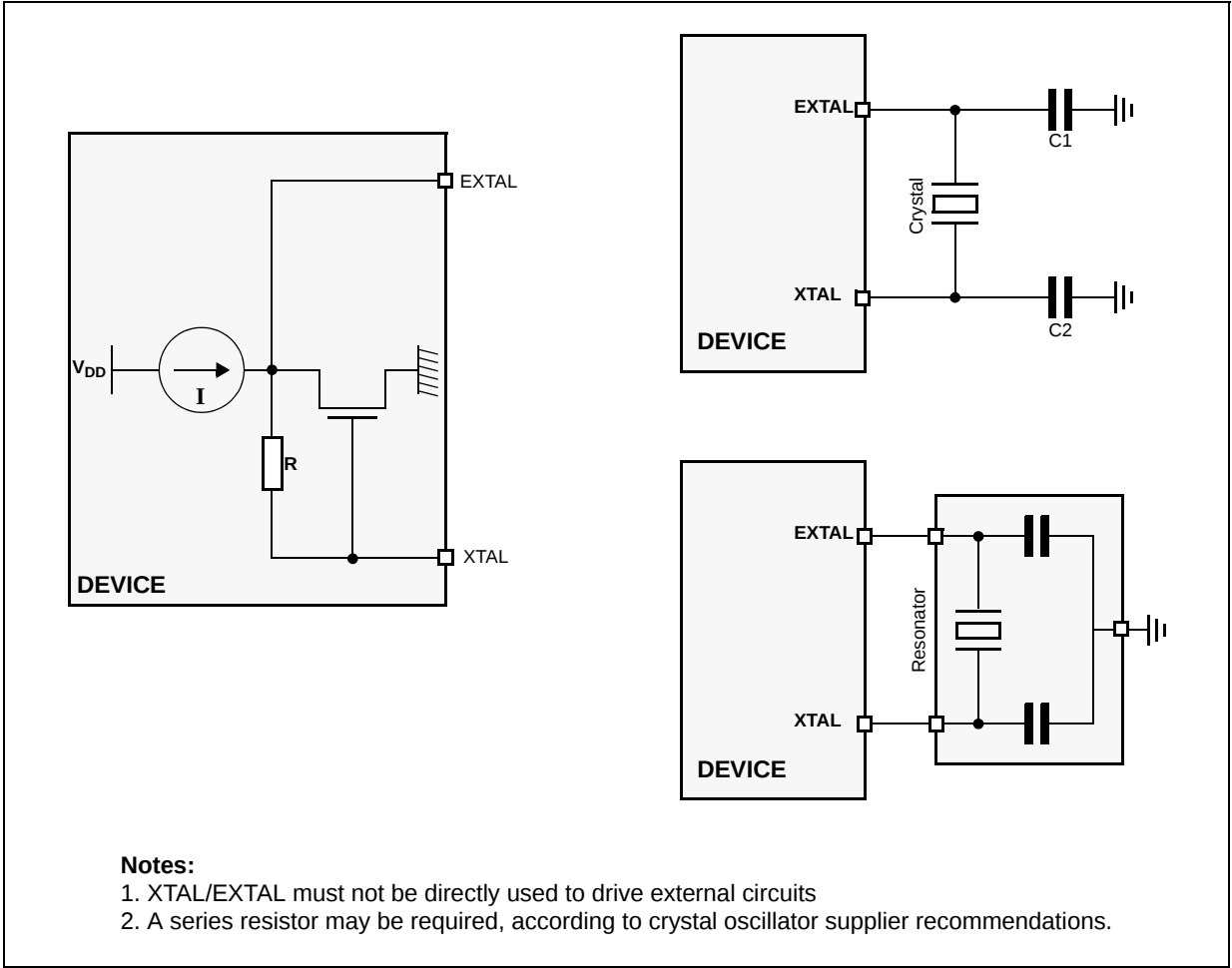


Table 37. Crystal description

Nominal frequency (MHz)	NDK crystal reference	Crystal equivalent series resistance ESR Ω	Crystal motional capacitance (C_m) fF	Crystal motional inductance (L_m) mH	Load on xtalin/xtalout $C1 = C2$ (pF) ⁽¹⁾	Shunt capacitance between xtalout and xtalin $C0$ ⁽²⁾ (pF)
4	NX8045GB	300	2.68	591.0	21	2.93
8	NX5032GA	300	2.46	160.7	17	3.01
10		150	2.93	86.6	15	2.91
12		120	3.11	56.5	15	2.93
16		120	3.90	25.3	10	3.00

1. The values specified for C1 and C2 are the same as used in simulations. It should be ensured that the testing includes all the parasitics (from the board, probe, crystal, etc.) as the AC / transient behavior depends upon them.
2. The value of C0 specified here includes 2 pF additional capacitance for parasitics (to be seen with bond-pads, package, etc.).

Figure 17. Slow external crystal oscillator (32 kHz) timing diagram

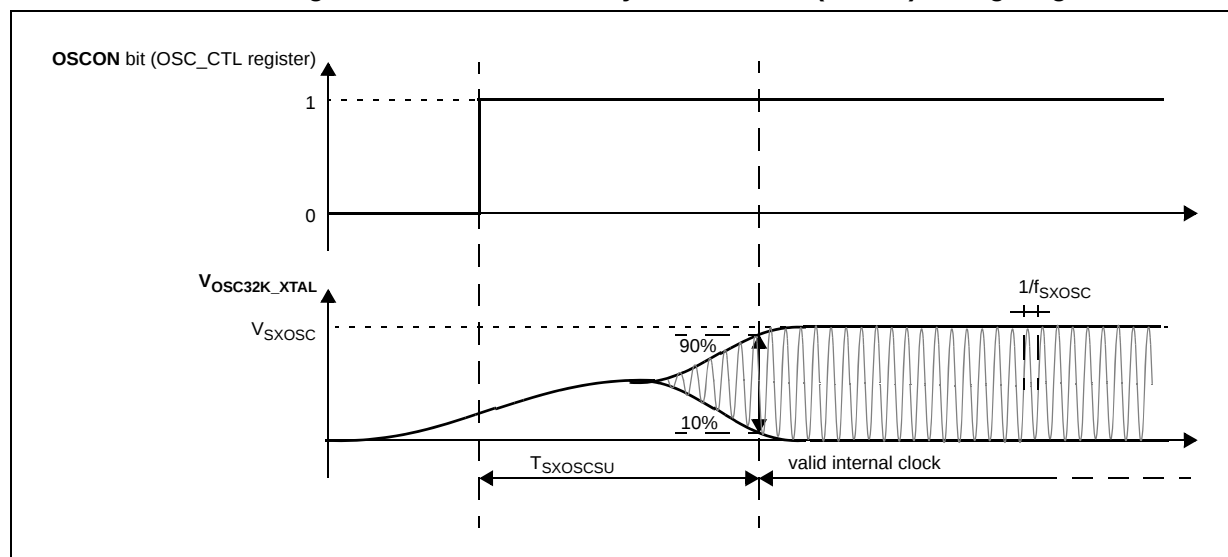


Table 40. Slow external crystal oscillator (32 kHz) electrical characteristics

Symbol	C	Parameter	Conditions ⁽¹⁾	Value			Unit
				Min	Typ	Max	
f_{SXOSC}	SR	—	Slow external crystal oscillator frequency	32	32.768	40	kHz
V_{SXOSC}	CC	T	Oscillation amplitude	—	2.1	—	V
$I_{SXOSCBias}$	CC	T	Oscillation bias current	—	2.5	—	μA
I_{SXOSC}	CC	T	Slow external crystal oscillator consumption	—	—	8	μA
$T_{SXOSCSU}$	CC	T	Slow external crystal oscillator start-up time	—	—	2 ⁽²⁾	s

1. $V_{DD} = 3.3\text{ V} \pm 10\% / 5.0\text{ V} \pm 10\%$, $T_A = -40$ to $125\text{ }^\circ\text{C}$, unless otherwise specified. Values are specified for no neighbor GPIO pin activity. If oscillator is enabled (OSC32K_XTAL and OSC32K_EXTAL pins), neighboring pins should not toggle.

2. Start-up time has been measured with EPSON TOYOCOM MC306 crystal. Variation may be seen with other crystal.

3.23 FMPLL electrical characteristics

The device provides a frequency-modulated phase-locked loop (FMPLL) module to generate a fast system clock from the main oscillator driver.

Table 41. FMPLL electrical characteristics

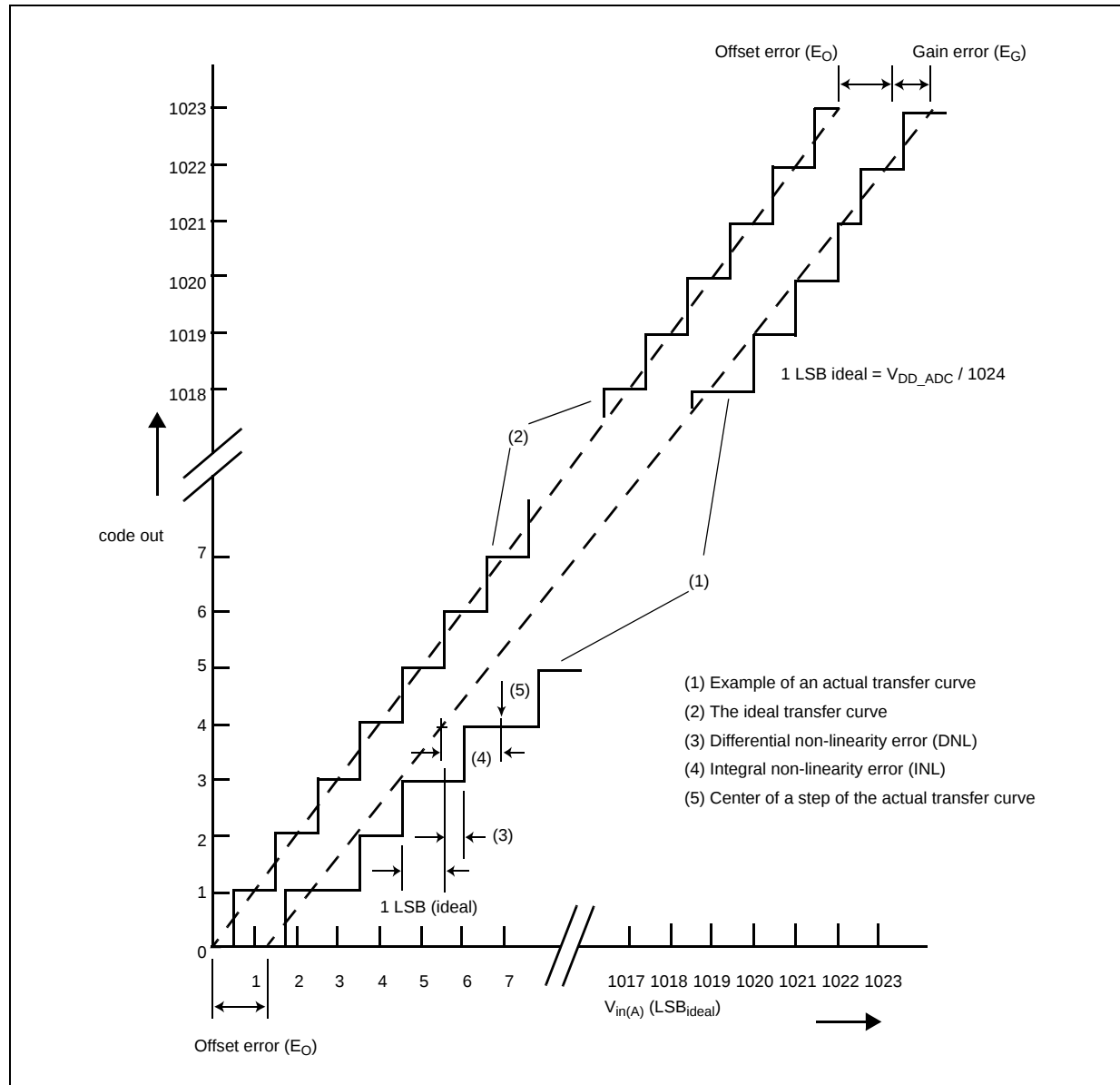
Symbol	C	Parameter	Conditions ⁽¹⁾	Value			Unit
				Min	Typ	Max	
f_{PLLIN}	SR	—	FMPLL reference clock ⁽²⁾	4	—	64	MHz
Δ_{PLLIN}	SR	—	FMPLL reference clock duty cycle ⁽²⁾	40	—	60	%
f_{PLLOUT}	CC	D	FMPLL output clock frequency	16	—	64	MHz

3.26 ADC electrical characteristics

3.26.1 Introduction

The device provides a 10-bit Successive Approximation Register (SAR) analog-to-digital converter.

Figure 18. ADC characteristic and error definitions



3.26.2 Input impedance and ADC accuracy

In the following analysis, the input circuit corresponding to the precise channels is considered.

To preserve the accuracy of the A/D converter, it is necessary that analog input pins have low AC impedance. Placing a capacitor with good high frequency characteristics at the input pin of the device can be effective: the capacitor should be as large as possible, ideally infinite. This capacitor contributes to attenuating the noise present on the input pin; furthermore, it sources charge during the sampling phase, when the analog signal source is a high-impedance source.

A real filter can typically be obtained by using a series resistance with a capacitor on the input pin (simple RC filter). The RC filtering may be limited according to the value of source impedance of the transducer or circuit supplying the analog signal to be measured. The filter at the input pins must be designed taking into account the dynamic characteristics of the input signal (bandwidth) and the equivalent input impedance of the ADC itself.

In fact a current sink contributor is represented by the charge sharing effects with the sampling capacitance: being C_S and C_{p2} substantially two switched capacitances, with a frequency equal to the conversion rate of the ADC, it can be seen as a resistive path to ground. For instance, assuming a conversion rate of 1 MHz, with $C_S + C_{p2}$ equal to 3 pF, a resistance of 330 k Ω is obtained ($R_{EQ} = 1 / (f_c \times (C_S + C_{p2}))$), where f_c represents the conversion rate at the considered channel). To minimize the error induced by the voltage partitioning between this resistance (sampled voltage on $C_S + C_{p2}$) and the sum of $R_S + R_F$, the external circuit must be designed to respect the [Equation 4](#):

Equation 4

$$V_A \cdot \frac{R_S + R_F}{R_{EQ}} < \frac{1}{2} \text{LSB}$$

[Equation 4](#) generates a constraint for external network design, in particular on a resistive path.

Figure 30. DSPI modified transfer format timing – slave, CPHA = 1

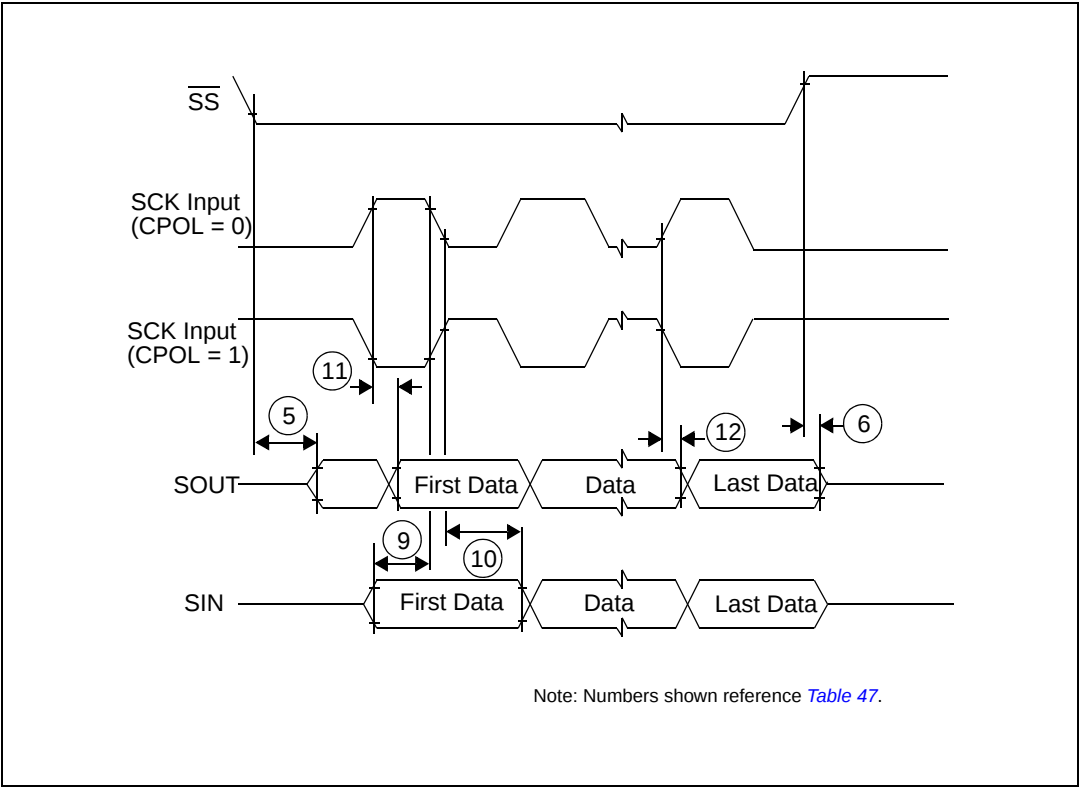
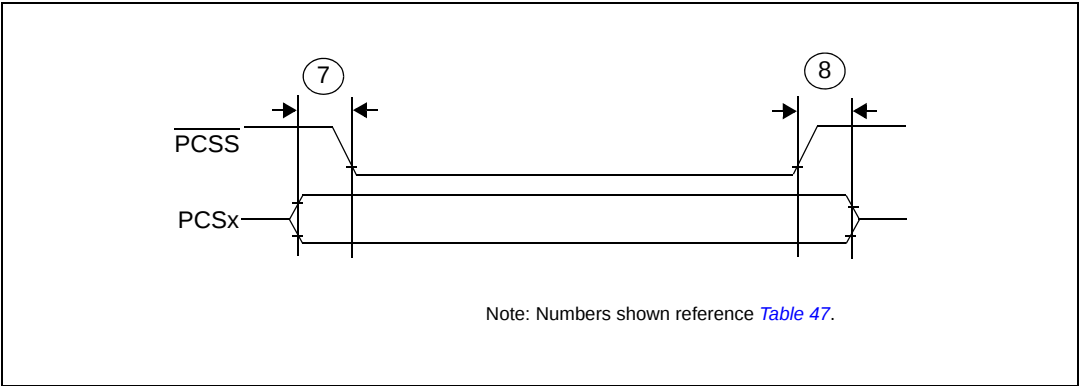


Figure 31. DSPI PCS strobe ($\overline{PCSS}$) timing



3.27.3 Nexus characteristics

Table 48. Nexus characteristics

No.	Symbol	C	Parameter	Value			Unit
				Min	Typ	Max	
1	t_{TCYC}	CC	D TCK cycle time	64	—	—	ns
2	t_{MCYC}	CC	D MCKO cycle time	32	—	—	ns
3	t_{MDOV}	CC	D MCKO low to MDO data valid	—	—	8	ns

4 Package characteristics

4.1 ECOPACK®

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.2 Package mechanical data

4.2.1 LQFP64

Figure 34. LQFP64 package mechanical drawing

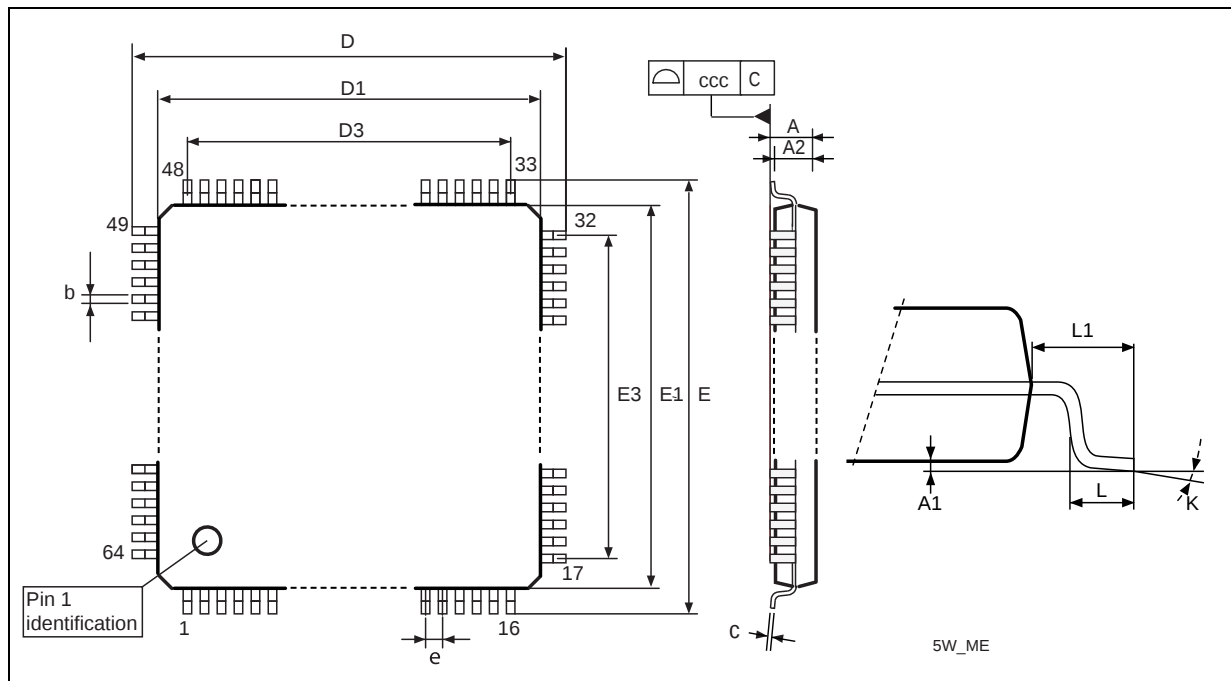


Table 50. LQFP64 mechanical data

Symbol	mm			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	—	—	1.6	—	—	0.063
A1	0.05	—	0.15	0.002	—	0.0059
A2	1.35	1.4	1.45	0.0531	0.0551	0.0571
b	0.17	0.22	0.27	0.0067	0.0087	0.0106
c	0.09	—	0.2	0.0035	—	0.0079
D	11.8	12	12.2	0.4646	0.4724	0.4803

Table 55. Document revision history (continued)

Date	Revision	Changes
06-Aug-2009	4	Updated "LBGA208 configuration" figure "Absolute maximum ratings" table: – V_{DD_ADC}, V_{IN}: changed min value for "relative to V_{DD}" condition – I_{CORELV}: added new row "Recommended operating conditions (5.0 V)" table: – T_A C-Grade Part, T_J C-Grade Part, T_A V-Grade Part, T_J V-Grade Part, T_A M-Grade Part, T_J M-Grade Part: added new rows – Changed capacitance value in footnote "Output pin transition times" table: – MEDIUM configuration: added condition for $PAD3V5V = 0$ Updated "Voltage regulator capacitance connection" "Voltage regulator electrical characteristics" table: – C_{DEC1}: changed min value – I_{MREG}: changed max value – I_{DD_BV}: added max value footnote "Low voltage monitor electrical characteristics" table: – $V_{LVDHV3H}$, $V_{LVDHV5H}$: changed max value – $V_{LVDHV3L}$, $V_{LVDHV5L}$: added max value Updated "Low voltage power domain electrical characteristics" table "Flash module life" table: – Retention: deleted min value footnote for "Blocks with 100000 P/E cycles" "Fast external crystal oscillator (4 to 16 MHz) electrical characteristics" table: – I_{FXOSC}: added typ value "Slow external crystal oscillator (32 kHz) electrical characteristics" table: – V_{SXOSC}: changed typ value – $T_{SXOSCSU}$: added max value footnote "FMPLL electrical characteristics" table – Δt_{LTJIT}: added max value Updated "LQFP100 package mechanical drawing"

Table 55. Document revision history (continued)

Date	Revision	Changes
18-Jan-2013	11	In the cover feature list, replaced "System watchdog timer" with "Software watchdog timer" Table 3 (SPC560B40x/50x and SPC560C40x/50x series block summary), replaced "System watchdog timer" with "Software watchdog timer" and specified AUTOSAR (Automotive Open System Architecture) Table 6 (Functional port pin descriptions), replaced VDD with VDD_HV Figure 9 (Voltage regulator capacitance connection), updated pin name appearance Renamed Figure 10 (V_{DD_HV} and V_{DD_BV} maximum slope) (was "VDD and VDD_BV maximum slope") and replaced VDD_HV(MIN) with VPORH(MAX) Renamed Figure 11 (V_{DD_HV} and V_{DD_BV} supply constraints during STANDBY mode exit) (was "VDD and VDD_BV supply constraints during STANDBY mode exit") Table 13 (Recommended operating conditions (3.3 V)), added minimum value of T_{VDD} and footnote about it. Table 14 (Recommended operating conditions (5.0 V)), added minimum value of T_{VDD} and footnote about it. Section 3.17.1, Voltage regulator electrical characteristics: replaced "slew rate of V_{DD}/V_{DD_BV}" with "slew rate of both V_{DD_HV} and V_{DD_BV}" replaced "When STANDBY mode is used, further constraints apply to the V_{DD}/V_{DD_BV} in order to guarantee correct regulator functionality during STANDBY exit." with "When STANDBY mode is used, further constraints are applied to the both V_{DD_HV} and V_{DD_BV} in order to guarantee correct regulator function during STANDBY exit." Table 28 (Power consumption on VDD_BV and VDD_HV), updated footnotes of I_{DDMAX} and I_{DDRUN} stating that both currents are drawn only from the V_{DD_BV} pin. Table 32 (Flash memory power supply DC electrical characteristics), in the parameter column replaced V_{DD_BV} and V_{DD_HV} respectively with VDD_BV and VDD_HV. Table 46 (On-chip peripherals current consumption), in the parameter column replaced V_{DD_BV}, V_{DD_HV} and $V_{DD_HV_ADC}$ respectively with VDD_BV, VDD_HV and VDD_HV_ADC Updated Section 3.26.2, Input impedance and ADC accuracy Table 47 (DSPI characteristics), modified symbol for t_{PCSC} and t_{PASC}
18-Sep-2013	12	Updated Disclaimer.
03-Feb-2015	13	In Table 2: SPC560B40x/50x and SPC560C40x/50x device comparison: – changed the MPC5604BxLH entry for CAN (FlexCAN) from 3⁷ to 2⁶. – updated tablenote 7. In Table 14: Recommended operating conditions (5.0 V), updated tablenote 5 to: "1 μF (electrolithic/tantalum) + 47 nF (ceramic) capacitance needs to be provided between V_{DD_ADC}/V_{SS_ADC} pair. Another ceramic cap of 10nF with low inductance package can be added". In Section 3.17.2: Low voltage detector electrical characteristics, added a note on LVHVD5 detector. In Section 5: Ordering information, added a note: "Not all options are available on all devices".